

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising[[:]] a source signal line driver circuit comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current ~~minor~~ mirror circuit and the differential circuit comprising at least [[a]] first and second thin film transistors; and

a third transistor electrically connected to the analog buffer;

wherein channel forming regions of the first and second thin film transistors, ~~each of the channel forming regions comprising~~ comprise a polycrystalline semiconductor layer, over a same substrate,

wherein a gate length of the first and second thin film transistors is twice or more as compared with a gate length of the third thin film transistor, and

wherein [[a]] the gate length of the first and second thin film transistors is 7  $\mu\text{m}$  or longer.

2. (Original) A semiconductor device according to claim 1, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

3. (Currently Amended) A semiconductor device comprising; a source signal line driver circuit comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current ~~minor~~ mirror circuit and the differential circuit comprising at least a first and second thin film transistors; and

a third transistor electrically connected to the analog buffer;

wherein channel forming regions of the first and second thin film transistors, each of the channel forming regions comprising a polycrystalline semiconductor layer, over a same substrate,

wherein a gate length of the first and second thin film transistors is twice or more as compared with a gate length of the third thin film transistor, and

wherein ~~[[a-]]~~the gate width of the first and second thin film transistors is 50  $\mu\text{m}$  or longer.

4. (Original) A semiconductor device according to claim 3, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

5. (Currently Amended) A semiconductor device comprising; a source signal line driver circuit comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current ~~mirror~~ mirror circuit and the differential circuit comprising at least a first and second thin film transistors; and

a third transistor electrically connected to the analog buffer;

wherein channel forming regions of the first and second thin film transistors, each of the channel forming regions comprising a polycrystalline semiconductor layer, over a same substrate,

wherein a gate length of the first and second thin film transistors is twice or more as compared with a gate length of the third thin film transistor, and

wherein the ~~[[a-]]~~gate length of the first and second thin film transistors is 7  $\mu\text{m}$  or longer and ~~[[a-]]~~the gate width of the first and second thin film transistors is 50  $\mu\text{m}$  or longer.

6. (Original) A semiconductor device according to claim 5, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation

system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

7-14. (Cancelled).

15. (Currently Amended) A semiconductor device comprising~~[[a]]~~a source signal line driver circuit comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current ~~minor-mirror~~ circuit and the differential circuit comprising at least a first and second thin film transistors, and

a third transistor electrically connected to the analog buffer;

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer, over a same substrate,

wherein a gate length of each of the first and second thin film transistors is 7  $\mu\text{m}$  or longer;

wherein the first and second thin film transistors are connected in parallel with each other; ~~and~~

wherein a gate length of the first and second thin film transistors is twice or more as compared with a gate length of the third thin film transistor, and

wherein ~~[[a]]~~the gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

16. (Original) A semiconductor device according to claim 15, wherein a gate width of the respective thin film transistors is 50  $\mu\text{m}$  or longer.

17. (Original) A semiconductor device according to claim 15, wherein the respective thin film transistors is a multi-gate type.

18. (Original) A semiconductor device according to claim 15, wherein the respective thin film transistors is a multi-gate type and a gate width of the respective thin film transistors is 50  $\mu\text{m}$  or longer.

19. (Original) A semiconductor device according to claim 15, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

20. (Currently Amended) A semiconductor device comprising~~[[a]]~~a source signal line driver circuit:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors, and

a third transistor electrically connected to the analog buffer;

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer, over the same substrate,

wherein a gate width of each of the first and second thin film transistors is 50  $\mu\text{m}$  or longer;

wherein the first and second thin film transistors are connected in parallel with each other; ~~and~~

wherein a gate length of the first and second thin film transistors is twice or more as compared with a gate length of the third thin film transistor, and

wherein ~~[[a]]~~the gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

21. (Original) A semiconductor device according to claim 20, wherein the respective thin film transistors is multi-gate type.

22. (Original) A semiconductor device according to claim 20, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

23. (Currently Amended) A semiconductor device comprising~~[[a]]~~a source signal line driver circuit:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors, and

a third transistor electrically connected to the analog buffer;

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer, over a same substrate,

wherein each of the first and second thin film transistors is multi-gate type

wherein the first and second thin film transistors are connected in parallel with each other; ~~and~~

wherein a gate length of the first and second thin film transistors is twice or more as compared with a gate length of the third thin film transistor, and

wherein ~~[[a]]~~the gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

24. (Original) A semiconductor device according to claim 23, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

25. (Original) A semiconductor device comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors,

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,

wherein a gate length of each of the first and second thin film transistors is 7  $\mu\text{m}$  or longer;

wherein the first and second thin film transistors are connected in parallel with each other and located in a cross arrangement; and

wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

26. (Original) A semiconductor device according to claim 25, wherein the device is selected from the group consisting of a liquid crystal display, an EL display a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

27. (Currently Amended) A semiconductor device comprising~~[[:-]]~~a source signal line driver circuit:

an analog buffer comprising a source follower comprising a plurality of thin film transistors; ~~and~~

a channel region of the respective thin film transistors, comprising a polycrystalline semiconductor layer, over a same substrate; and

a third transistor electrically connected to the analog buffer;

wherein the respective thin film transistors is a multi-gate type;

wherein a gate length of the respective thin film transistors is 7  $\mu\text{m}$  or longer and a gate width of the respective thin film transistors is 50  $\mu\text{m}$  or longer;

wherein the plurality of thin film transistors are connected in parallel with each other,  
~~and~~

wherein the gate length of the respective thin film transistors is twice or more as  
compared with a gate length of the third thin film transistor, and

wherein gate electrodes of the plurality of thin film transistors are connected to a same  
potential.

28. (Original) A semiconductor device according to claim 27, wherein the device  
is selected from the group consisting of a liquid crystal display, an EL display, a video  
camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation  
system, a sound reproduction device, a note type personal computer, a game device, a  
portable information terminal, an image playback device having a recording medium.